

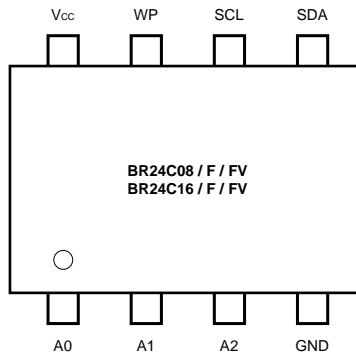
# I<sup>2</sup>C Bus compatible serial EEPROM

**BR24C08 / BR24C08F / BR24C08FV /  
BR24C16 / BR24C16F / BR24C16FV** **under  
development**

## ●Features

- Wide range of operating power supply voltages (2.7V to 5.5V).
- 2-wire serial interface.
- Auto erase and auto completion function when writing data.
- Page write mode function:16byte
- Low current consumption.
  - Operating (at 5V) : 2.0mA (typ.)
  - Standby (at 5V) : 1.0μA (typ.)
- Write protect function.
  - Equipped with WP (write protect) function.
  - Writing disabled when power supply voltage is low.
- Compact DIP8, SOP8, and SSOPB8 packages.
- Highly reliable COMS processing.
- Rewriting possible up to 100,000 times.
- Data can be stored for ten years without corruption.
- Built-in noise filters at SCL and SDA pins.

## ●Pin assignments



## ●Overview

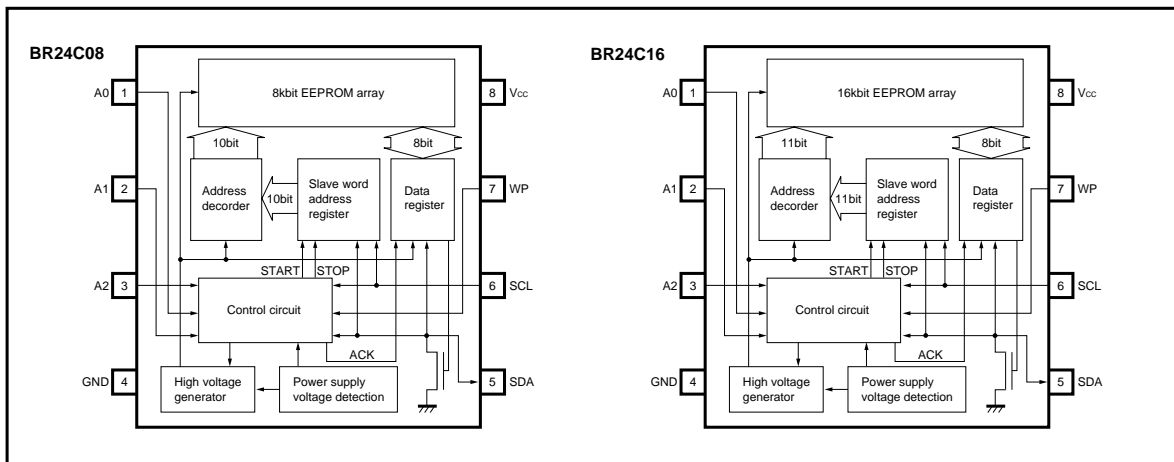
The BR24C08, BR24C08F, BR24C08FV, BR24C16, BR24C16F, and BR24C16FV are 2-wire (I<sup>2</sup>C bus type) serial EEPROMs which are electrically programmable.

The configurations are as follows:

BR24C08 / F / FV: 1k × 8 bit 1k serial EEPROM

BR24C16 / F / FV: 2k × 8 bit 2k serial EEPROM

## ●Block diagram



## ●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Applied voltage	V <sub>CC</sub>	- 0.3 ~ + 6.5	V
Power dissipation	P <sub>d</sub>	300 (SSOP8)* <sup>1</sup> 350 (SOP8)* <sup>2</sup> 500 (DIP8)* <sup>3</sup>	mW
Storage temperature	T <sub>stg</sub>	- 65 ~ + 125	°C
Operating temperature	T <sub>opr</sub>	- 40 ~ + 85	°C
Pin voltages	—	- 0.3 ~ V <sub>CC</sub> + 0.3	V

\*1 Reduced by 3.0mW for each increase in Ta of 1 °C over 25°C.

\*2 Reduced by 3.5mW for each increase in Ta of 1 °C over 25°C.

\*3 Reduced by 5.0mW for each increase in Ta of 1 °C over 25°C.

## ●Recommended operating conditions (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Power supply voltage	V <sub>CC</sub>	2.7 ~ 5.5	V
Input voltage	V <sub>IN</sub>	0 ~ V <sub>CC</sub>	V

●Electrical characteristics (unless otherwise noted,  $T_a = -40$  to  $+85^\circ\text{C}$ ,  $V_{CC} = 2.7\text{V}$  to  $5.5\text{V}$ )

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Input high level voltage	$V_{IH}$	$0.7V_{CC}$	—	—	V	—
Input low level voltage	$V_{IL}$	—	—	$0.3V_{CC}$	V	—
Output low level voltage	$V_{OL}$	—	—	0.4	V	$I_{OL} = 3.0\text{mA}$ (SDA)
Input leakage current	$I_{LI}$	-1	—	1	$\mu\text{A}$	$V_{IN} = 0\text{V} \sim V_{CC}$
Output leakage current	$I_{LO}$	-1	—	1	$\mu\text{A}$	$V_{OUT} = 0\text{V} \sim V_{CC}$
Operating current consumption	$I_{CC}$	—	—	3.0	mA	$V_{CC} = 5.5\text{V}$ , $f_{SCL} = 400\text{kHz}$
Standby current	$I_{SB}$	—	—	3.0	$\mu\text{A}$	$V_{CC} = 5.5\text{V}$ , SDA • SCL = $V_{CC}$ A0, A1, A2 = GND WP = GND

○ Not designed for radiation resistance.

●Operating timing characteristics (unless otherwise noted,  $T_a = -40$  to  $+85^\circ\text{C}$ ,  $V_{CC} = 2.7\text{V}$  to  $5.5\text{V}$ )

Parameter	Symbol	$V_{CC} = 5\text{V} \pm 10\%$			$V_{CC} = 3\text{V} \pm 10\%$			Unit
		Min.	Typ.	Max.	Min.	Typ.	Max.	
SCL frequency	$f_{SCL}$	—	—	400	—	—	100	kHz
Data clock high time	$t_{HIGH}$	0.6	—	—	4.0	—	—	$\mu\text{s}$
Data clock low time	$t_{LOW}$	1.2	—	—	4.7	—	—	$\mu\text{s}$
SDA / SCL rise time	$t_r$	—	—	0.3	—	—	1.0	$\mu\text{s}$
SDA / SCL fall time	$t_f$	—	—	0.3	—	—	0.3	$\mu\text{s}$
Start condition hold time	$t_{HD}$ : STA	0.6	—	—	4.0	—	—	$\mu\text{s}$
Start condition setup time	$t_{SU}$ : STA	0.6	—	—	4.7	—	—	$\mu\text{s}$
Input data hold time	$t_{HD}$ : DAT	0	—	—	0	—	—	ns
Input data setup time	$t_{SU}$ : DAT	100	—	—	250	—	—	ns
Output data delay time	$t_{PD}$	0.1	—	0.9	0.2	—	3.5	$\mu\text{s}$
Output data hold time	$t_{DH}$	0.1	—	—	0.2	—	—	$\mu\text{s}$
Stop condition setup time	$t_{SU}$ : STO	0.6	—	—	4.7	—	—	$\mu\text{s}$
Bus open time before start of transfer	$t_{BUF}$	1.2	—	—	4.7	—	—	$\mu\text{s}$
Internal write cycle time	$t_{WR}$	—	—	10	—	—	10	ms
Noise erase valid time (SDA / SCL pins)	$t_i$	—	—	0.05	—	—	0.1	$\mu\text{s}$

● External dimensions (Units: mm)

